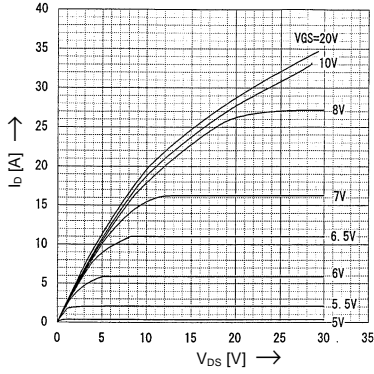


> Characteristics

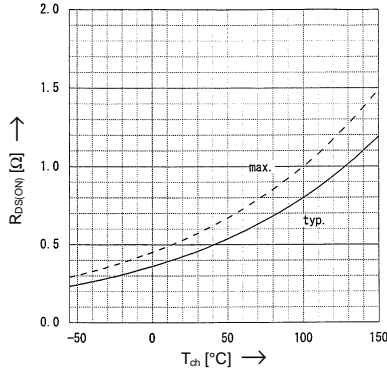
Typical Output Characteristics

$I_D=f(V_{DS})$; 80μs pulse test; $T_{ch}=25^{\circ}C$



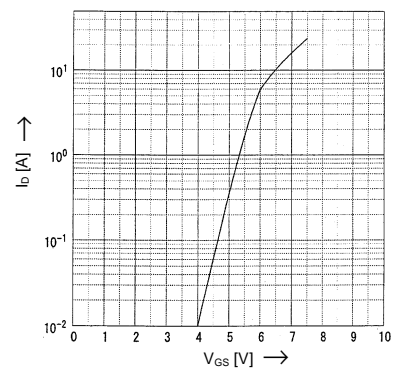
Drain-Source On-State Resistance vs. T_{ch}

$R_{DS(on)}=f(T_{ch})$; $I_D=7,5A$; $V_{GS}=10V$



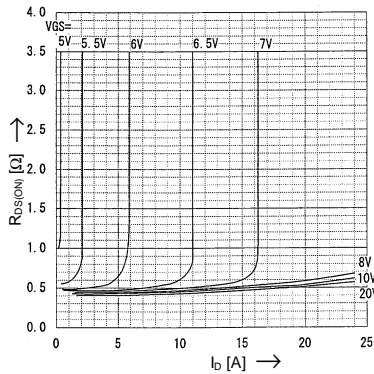
Typical Transfer Characteristics

$I_D=f(V_{GS})$; 80μs pulse test; $V_{DS}=25V$; $T_{ch}=25^{\circ}C$



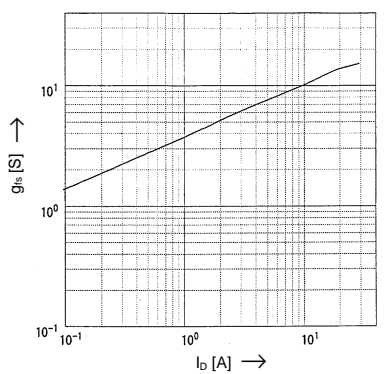
Typical Drain-Source On-State-Resistance vs. I_D

$R_{DS(on)}=f(I_D)$; 80μs pulse test; $T_{ch}=25^{\circ}C$



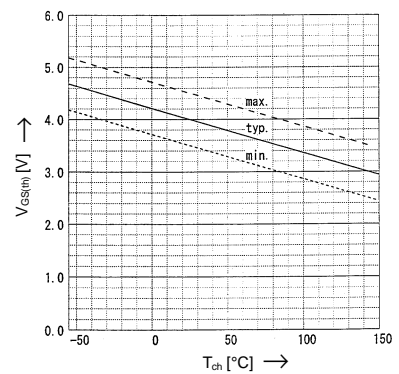
Typical Forward Transconductance vs. I_D

$g_{fs}=f(I_D)$; 80μs pulse test; $V_{DS}=25V$; $T_{ch}=25^{\circ}C$



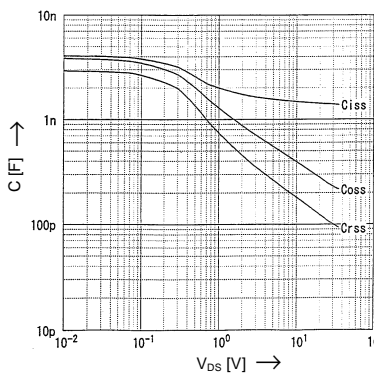
Gate Threshold Voltage vs. T_{ch}

$V_{GS(th)}=f(T_{ch})$; $I_D=1mA$; $V_{DS}=V_{GS}$



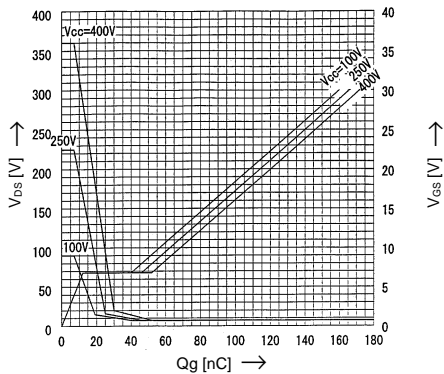
Typical Capacitances vs. V_{DS}

$C=f(V_{DS})$; $V_{GS}=0V$; $f=1MHz$



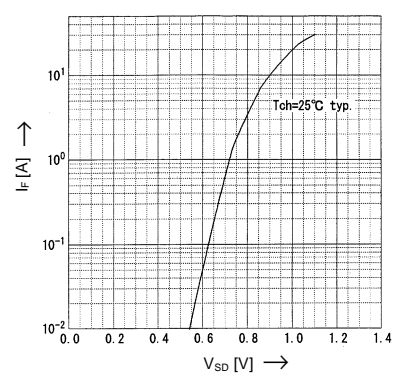
Typical Gate Charge Characteristic

$V_{GS}=f(Q_g)$; $I_D=15A$; $T_{ch}=25^{\circ}C$



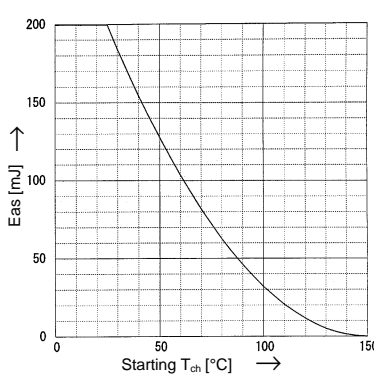
Forward Characteristics of Reverse Diode

$I_F=f(V_{SD})$; 80μs pulse test; $V_{GS}=0V$



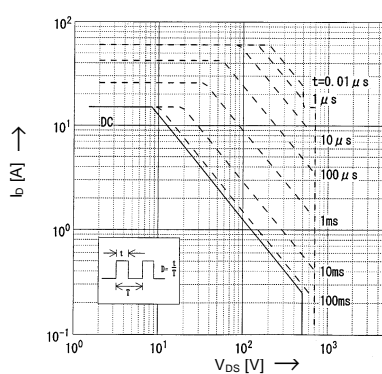
Avalanche Energy Derating

$E_{as}=f(\text{starting } T_{ch})$; $V_{CC}=50V$; $I_{AV}=15A$



Safe Operation Area

$I_D=f(V_{DS})$; $D=0,01$; $T_{ch}=25^{\circ}C$



Transient Thermal impedance
 $Z_{th(ch-e)}=f(t)$ parameter: $D=t/T$

